#### TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

# 2SK3077

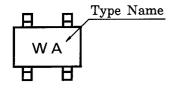
## 900 MHz BAND AMPLIFIER APPLICATIONS (GSM)

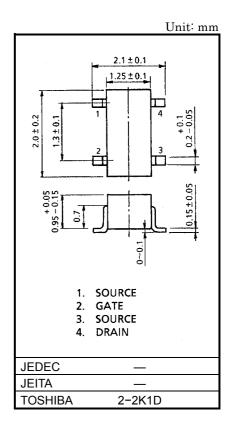
## **MAXIMUM RATINGS (Ta = 25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	10	V
Gate-Source Voltage	$V_{GSS}$	5	V
Drain Current	I <sub>D</sub>	0.1	Α
Power Dissipation	P <sub>D*</sub>	0.1	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-45~150	°C

<sup>\*:</sup> Tc = 25°C When mounted on a 1.6 mm glass epoxy PCB

## **MARKING**





## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

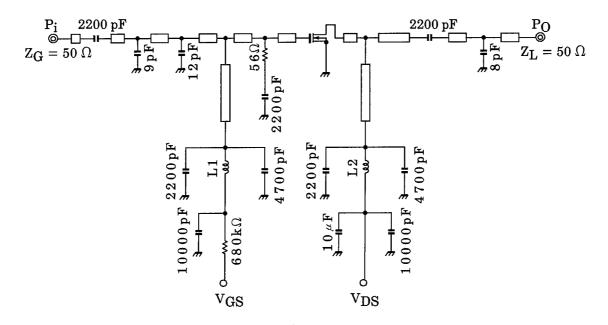
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Output Power	PO	$V_{DS}$ = 4.8V lidle = 43 mA ( $V_{GS}$ = adjust)	15.0	_	_	dBmW
Drain Efficiency	$\eta_{D}$		1	20.0	1	%
Power Gain	G <sub>P</sub>	f = 915 MHz, P <sub>i</sub> = 0 dBmW	15.0	_	_	dB
Threshold Voltage	$V_{th}$	$V_{DS} = 4.8 \text{ V}, I_D = 0.5 \text{ mA}$	0.25	_	1.25	V
Drain Cut-off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V	_	_	10	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = 5 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	5	μΑ

#### **CAUTION**

This transistor is the electrostatic sensitive device.

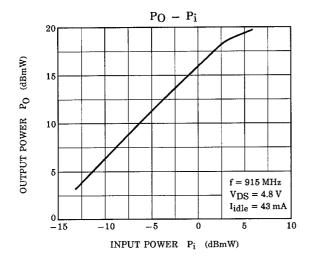
Please handle with caution.

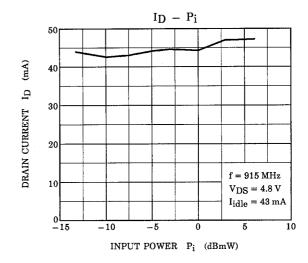
#### RF OUTPUT POWER TEST FIXTURE

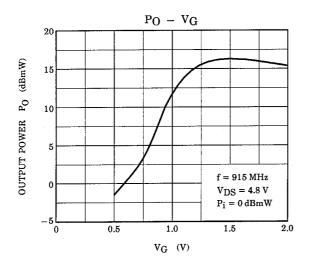


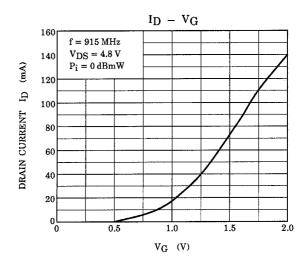
2

L1 :  $\phi$ 0.6 mm, 5.5 mmID, 5T L2 :  $\phi$ 0.6 mm, 5.5 mmID, 8T









### **CAUTION**

These are only typical curves and devices are not necessarily guaranteed at these curves.

3 2001-12-26

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